

NOT RECOMMENDED FOR NEW DESIGN USE DMN3025SFV



DMG7408SFG

30V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C		
	23mΩ @ V _{GS} = 10V	7.0A		
30V	$33m\Omega$ @ $V_{GS} = 4.5V$	6.0A		

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low R_{DS(ON)} Ensures On State Losses Are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of The Board Area Occupied by SO-8 Enabling Smaller End Product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

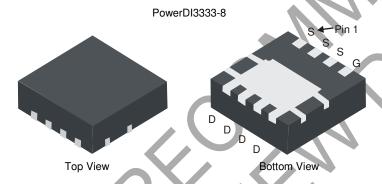
Description and Applications

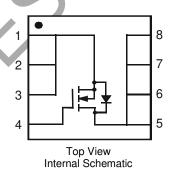
This MOSFET has been designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)





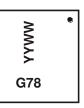
Ordering Information (Note 4)

Part Number	Case	Packaging
DMG7408SFG-7	PowerDI3333-8	2000/Tape & Reel
DMG7408SFG-13	PowerDI3333-8	3000/Tape & Reel

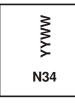
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



G78 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 17 = 2017) WW = Week Code (01 to 53)



N34 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 17 = 2017) WW = Week Code (01 to 53)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note E) V 10V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	7.0 5.5	Α
Continuous Drain Current (Note 5) V _{GS} = 10V	t<10s	$T_A = +25$ °C $T_A = +70$ °C	I _D	9.5 7.5	Α
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	6.0 5.7	Α
Continuous Drain Current (Note 5) V _{GS} = 4.5V	t<10s	$T_A = +25$ °C $T_A = +70$ °C	I _D	8.0 6.3	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	66	Α		
Maximum Continuous Body Diode Forward Current (I _S	3.0	Α		
Avalanche Current (Note 7)	las	9	Α		
Avalanche Energy (Note 7)	E _{AS}	12	mJ		

Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)		P _D	1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	131	°C/W
Thermal resistance, variotion to runbient (Note 6)	t<10s	ПфЈА	72	°C/W
Total Power Dissipation (Note 5)		PD	2.1	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	P	63	°C/W
Thermal resistance, buildion to Ambient (Note 3)	t<10s	$R_{\theta JA}$	35	°C/W
Thermal Resistance, Junction to Case (Note 5)		$R_{ heta JC}$	7.1	°C/W
Operating and Storage Temperature Range		T_{J} , T_{STG}	-55 to +150	°C

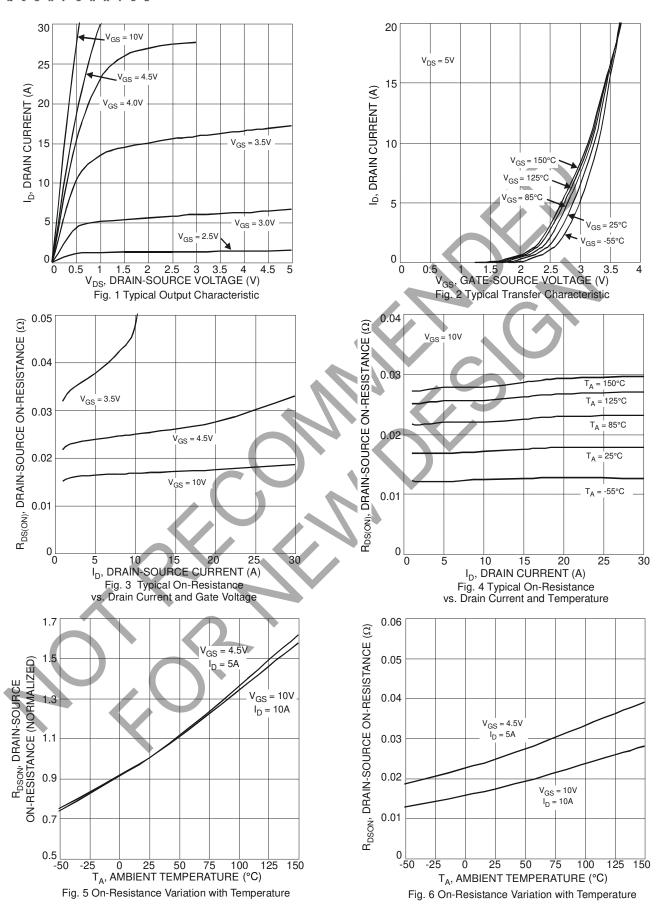
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}		1	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	- 4	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	1.0	1.45	2.4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance			15	23 33	mΩ	$V_{GS} = 10V, I_D = 10A$	
Static Drain-Source On-nesistance	R _{DS(ON)}	-	25			$V_{GS} = 4.5V, I_D = 7.5A$	
Forward Transfer Admittance	Y _{fs}	-	11	-	S	$V_{DS} = 5V, I_{D} = 10A$	
Diode Forward Voltage	V_{SD}	-	0.72	1	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	-	478.9	-	pF		
Output Capacitance	Coss	-	96.7	-	рF	V _{DS} = 15V, V _{GS} = 0V, -f = 1.0MHz	
Reverse Transfer Capacitance	Crss	-	61.4	-	pF	1 – 1.000112	
Gate Resistance	R_g	0.4	1.1	1.6	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	5.0	8	-C		
Total Gate Charge (V _{GS} = 10V)	Q_g	-	10.5	17	nC V 15VI 10A		
Gate-Source Charge	Q _{gs}	-	1.8	-	nC	$V_{DS} = 15V, I_{D} = 10A$	
Gate-Drain Charge	Q_{gd}	-	1.6	-	nC	1	
Turn-On Delay Time	t _{D(ON)}	-	2.9	-	ns	V _{GS} = 10V, V _{DS} = 15V,	
Turn-On Rise Time	t _R	-	7.9	-	ns		
Turn-Off Delay Time	t _{D(OFF)}	-	14.6	-	ns	$R_G = 3\Omega$, $R_L = 1.5\Omega$	
Turn-Off Fall Time	t _F	-	3.1	-	ns		

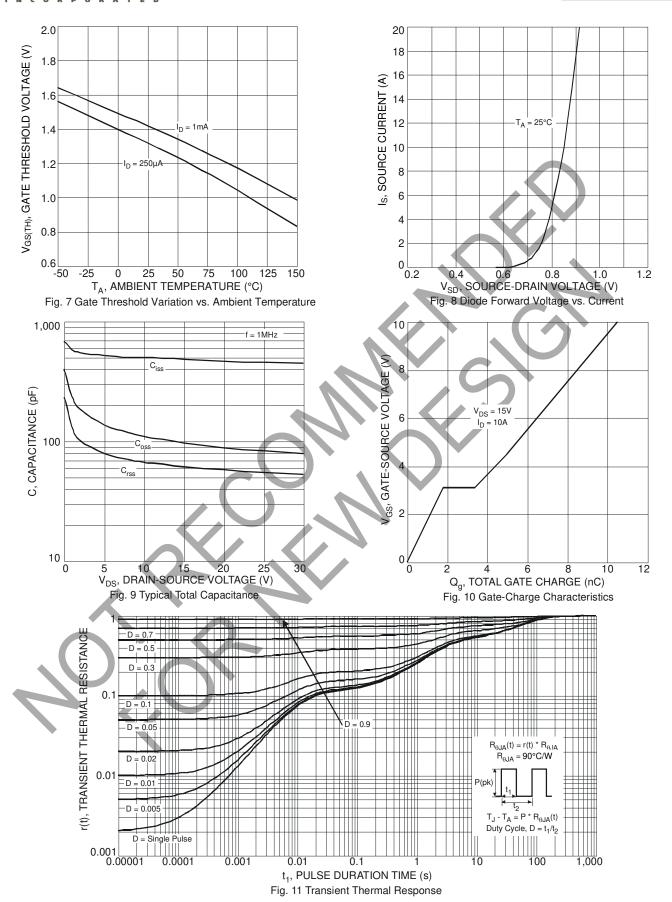
Notes:

- 5. R_{0JA} is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 7. UIS in production with L = 0.3mH, T_J = +25°C.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.







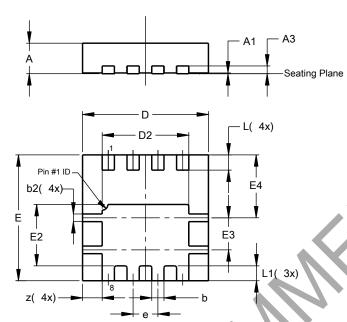




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

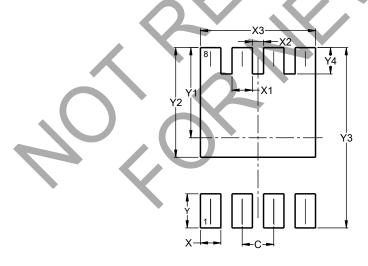


PowerDI3333-8						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	0.02			
A3	_	_	0.203			
b	0.27	0.37	0.32			
b2	0.15	0.25	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
Е	3.25	3.35	3.30			
E2	1.56	1.66	1.61			
E3	0.79	0.89	0.84			
E4	1.60	1.70	1.65			
е	_	_	0.65			
L	0.35	0.45	0.40			
L1	_	_	0.39			
Z	_	_	0.515			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
С	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700
V4	0.540



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